Onsemi

Switch-mode **Power Rectifiers**

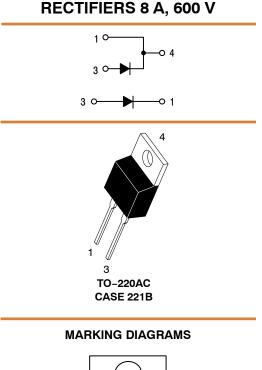
NHPV08S600G

Features

- Ultrafast 30 Nanosecond Recovery Time
- 150°C Operating Junction Temperature
- High Voltage Capability of 600 V
- Low Forward Drop
- Low Leakage Specified @ 125°C Case Temperature
- This Device is Pb-Free and RoHS Compliant

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



PLANAR ULTRAFAST



= Assembly Location

= Year

А Y

- ww = Work Week G
- = Pb-Free Package KA
 - = Diode Polarity

ORDERING INFORMATION

| Device | Package | Shipping |
|-------------|-----------------------|-----------------|
| NHPV08S600G | TO-220AC (Pb-Free) | 50 Units / Rail |

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NHPV08S600G

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|--|------------------------------|------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V _{RRM} V _{RWM} V _R | 600 | V |
| Average Rectified Forward Current (Rated V _R) | I _{F(AV)} | 8 A @ T _C = 130°C | Α |
| Peak Rectified Forward Current (Rated V _R , Square Wave, 20 kHz) | I _{FRM} | 8 A @ T _C = 125°C | А |
| Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | I _{FSM} | 80 | A |
| Operating Junction Temperature and Storage Temperature Range | T _J , T _{stg} | –55 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|--|---------------------|-------|------|
| NHPV08S600G: Thermal Resistance Junction-to-Case (Note 1) | $R_{	ext{	heta}JC}$ | 1.5 | °C/W |
| NHPJ08S600G: Thermal Resistance Junction-to-Case (Note 1) | $R_{\theta JC}$ | 4.25 | °C/W |

1. Junction-to-Case shown as a typical value using a fixed 25°C cold plate boundary.

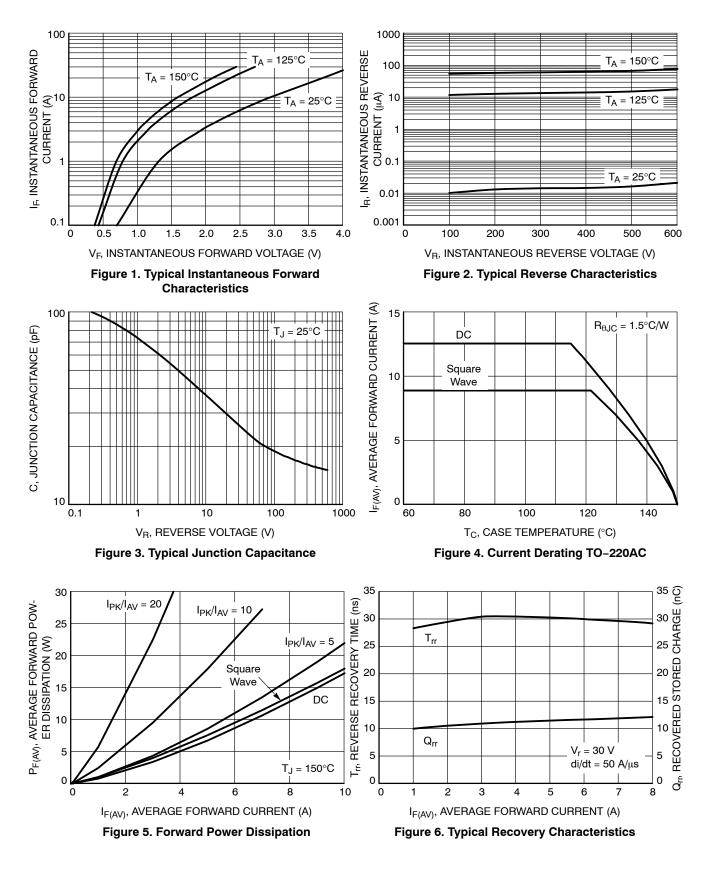
ELECTRICAL CHARACTERISTICS

| Characteristic | Test Conditions | Symbol | Тур | Max | Unit |
|--|---|--|--------------------------|--------------------|--------------------|
| Instantaneous Forward Voltage (Note 2) | (I _F = 8 A, T _C = 125°C) (I _F = 8 A, T _C = 25°C) | V _F | 1.5 2.7 | 1.8 3.2 | V |
| Instantaneous Reverse Current (Note 2) | (Rated DC Voltage, $T_C = 125^{\circ}C$) (Rated DC Voltage, $T_C = 25^{\circ}C$) | I _R | 46 0.1 | 400 30 | μΑ |
| Reverse Recovery Time | (I _F = 0.5 A, I _{rr} = 0.25 A, I _R = 1 A) (I _F = 1 A, dI _F /dt = -50 A/µs, V _R = 30 V) | t _{rr} | | 30 50 | ns |
| Reverse Recovery Time Peak Reverse Recovery Current Total Reverse Recovery Charge Softness Factor | $(I_F = 8 \text{ A}, d_{IF}/d_t = -200 \text{ A}/\mu \text{s}, T_C = 25^{\circ}\text{C})$ | t _{rr} I _{RM} Q _{rr} S | 30 2.3 37 2 | 50 3 50 - | ns A nC - |
| Reverse Recovery Time Peak Reverse Recovery Current Total Reverse Recovery Charge Softness Factor | $(I_F = 8 \text{ A}, d_{IF}/d_t = -200 \text{ A}/\mu \text{s}, T_C = 125^{\circ}\text{C})$ | t _{rr} I _{RM} Q _{rr} S | 45 5.5 150 0.35 | - - - - | ns A nC - |
| Forward Recovery Time Peak Forward Recovery Voltage | $(I_F = 8 \text{ A}, d_{IF}/d_t = 120 \text{ A}/\mu\text{s}, T_C = 25^{\circ}\text{C})$ | t _{fr} V _{FP} | - | 200 6 | ns V |

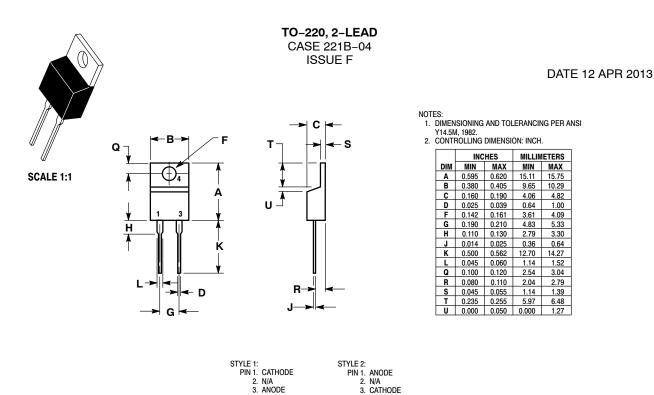
2. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

NHPV08S600G

TYPICAL CHARACTERISTICS







4. ANODE

4. CATHODE

| DOCUMENT NUMBER: | 98ASB42149B | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. | | |
|------------------|----------------|---|-------------|--|
| DESCRIPTION: | TO-220, 2-LEAD | | PAGE 1 OF 1 | |
| | | | | |

ON Semiconductor and (1) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters, including "Typicals" must be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcula performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative